

SECRET

Please cancel claims 1-24. Please add new claims 25-38
as follows:

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26. (NEW) The structure of claim 25, further comprising a layer of silicon, wherein the layer of cobalt disilicide is on the layer of silicon.

27. (NEW) The structure of claim 26, wherein the layer of cobalt disilicide is in contact with a reagent comprising water, ammonium hydroxide, and hydrogen peroxide.

28. (NEW) A structure, comprising:

a layer of cobalt disilicide, wherein the layer of cobalt disilicide is substantially free of cobalt monosilicide;

a patch of an oxide of titanium, wherein the patch is on the layer of cobalt disilicide; and

a reagent in contact with the patch at a temperature, wherein the reagent is adapted to remain in contact with the patch for a period of time, wherein the reagent removes the patch within the period of time, wherein the reagent does not chemically react with the layer of cobalt disilicide, and wherein the reagent comprises water, ammonium hydroxide, and hydrogen peroxide.

29. (NEW) The structure of claim 28, wherein:

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the ammonium hydroxide comprises approximately 4 percent of a total reagent volume of the reagent,

the hydrogen peroxide comprises approximately 4 percent of the total reagent volume,

the temperature is approximately between 45 degrees celsius and 95 degrees celsius, and

the period of time is approximately between 30 seconds and 10 minutes.

30. (NEW) The structure of claim 28, further comprising a layer of silicon, wherein the layer of cobalt disilicide is on the layer of silicon.

31. (NEW) The structure of claim 30, wherein a minimum period of time for removing the patch is inversely dependent on the temperature.

32. (NEW) A structure having a substrate, wherein the substrate includes:

an insulated-gate field effect transistor (FET), wherein the FET includes a source, a drain, and a gate;

a first layer of cobalt disilicide on the source, said first layer having substantially no cobalt monosilicide, and

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said first layer having substantially no stringer of an oxide of titanium thereon;

a second layer of cobalt disilicide on the drain, said second layer having substantially no cobalt monosilicide, and said second layer having substantially no stringer of an oxide of titanium thereon; and

a third layer of cobalt disilicide on the gate, said third layer having substantially no cobalt monosilicide, and said third layer having substantially no stringer of an oxide of titanium thereon.

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33. (NEW) The structure of claim 32, further comprising:

a first insulating structure bordering a side of the source and bordering a side of the first layer of cobalt disilicide; and

a second insulating structure bordering a side of the drain and bordering a side of the second layer of cobalt disilicide.

34. (NEW) The structure of claim 32, wherein the first layer of cobalt disilicide, the second layer of cobalt disilicide, and the third layer of cobalt disilicide are each in contact with a reagent comprising water, ammonium hydroxide, and

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hydrogen peroxide.

35. (NEW) A structure having a substrate, wherein the substrate includes:

an insulated-gate field effect transistor (FET), wherein the FET includes a source, a drain, and a gate;

a first layer of cobalt disilicide on the source, said first layer having substantially no cobalt monosilicide;

a second layer of cobalt disilicide on the drain, said second layer having substantially no cobalt monosilicide;

a third layer of cobalt disilicide on the gate, said third layer having substantially no cobalt monosilicide;

a patch of an oxide of titanium on a region of cobalt disilicide, said region selected from the group consisting of the first layer of cobalt disilicide, the second layer of cobalt disilicide, the third layer of cobalt disilicide, and combinations thereof;

a reagent in contact with the patch at a temperature, wherein the reagent is adapted to remain in contact with the patch for a period of time, wherein the reagent removes the patch within the period of time, wherein the reagent does not chemically react with the first layer of cobalt disilicide, wherein the reagent does not chemically react

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with the second layer of cobalt disilicide, wherein the reagent does not chemically react with the third layer of cobalt disilicide, and wherein the reagent comprises water, ammonium hydroxide, and hydrogen peroxide.

36. (NEW) The structure of claim 35, wherein:

the ammonium hydroxide comprises approximately 4 percent of a total reagent volume of the reagent,

the hydrogen peroxide comprises approximately 4 percent of the total reagent volume,

the temperature is approximately between 45 degrees celsius and 95 degrees celsius, and

the period of time is approximately between 30 seconds and 10 minutes.

37. (NEW) The structure of claim 35, further comprising:

a first insulating structure bordering a side the source and bordering a side of the first layer of cobalt disilicide; and

a second insulating structure bordering a side of the drain and bordering a side of the second layer of cobalt disilicide.